10/763,334

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L17	0	(semiconductor testing AND semiconductor storage device AND counters AND switching circuit AND write operation AND read operation AND address signal AND most significant bit AND least significant bit AND synchronous counter AND asynchronous counter AND counter selection circuit AND counter control signal AND built-in self test AND BIST AND self testing circuit AND semiconductor storage device AND semiconductor chip).clm.	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/01/26 15:40

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	77274	(switching circuit or controller circuit or multiplexing circuit or multiplexer or MUX or selector circuit) and counter$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:32
L2	976	counter$1 same counter control signal$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:32
L3	80	(switching circuit or controller circuit or multiplexing circuit or multiplexer or MUX or selector circuit) same L2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:32
L4	80	L3 and L1	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:32
L5	76	semiconductor testing circuit or testing semiconductor storage device	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:33
L6	1	L5 and L3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:33
L8	7912	counter$1 same (most significant bit$1 or lest significant bit$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:34

EAST Search History

L9	1093597	address$2 or address group$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:33
L10	5070	L8 and L9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:33
L11	1093597	address$2 or address group$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:34
L12	47	write operation same read operation same semiconductor storage device	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:34
L13	1143359	asynchronous counter$1 or synchronous counter$1 or counter$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:34
L14	80	L4 and L13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:34
L15	36133	714/718 or 714/706 or 714/707 or 714/799 or 365/200 or 365/201 or 365/189.01 or 365/189.02 or 365/230.01 or 365/230.02 or 365/230.05 or 365/236 or 365/? or 714/776 or 714/733 or 714/734 or 714/724 or 714/?	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:36

EAST Search History

L16	11150	built-in self test or BIST or built-in test or in-circuit test or memory self-test or semiconductor testing	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:37
L17	0	(semiconductor testing AND semiconductor storage device AND counters AND switching circuit AND write operation AND read operation AND address signal AND most significant bit AND least significant bit AND synchronous counter AND asynchronous counter AND counter selection circuit AND counter control signal AND built-in self test AND BIST AND self testing circuit AND semiconductor storage device AND semiconductor chip).clm.	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/01/26 15:40
L18	5070	l10 and l11	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:40
L19	9	l18 and l14	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:40
L20	1	l19 and l16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/01/26 15:40